



SRAM MODULE 512KByte (128K x 32-Bit)
Part No. HMS12832M4

GENERAL DESCRIPTION

The HMS12832M4 is a high-speed static random access memory (SRAM) module containing 131,072 words organized in a x32-bit configuration. The module consists of four 128K x 8 SRAMs mounted on a 64-pin, single-sided, FR4-printed circuit board.

PD0 and PD1 identify the module's density allowing interchangeable use of alternate density, industry-standard modules. Four chip enable inputs, (/CE1, /CE2, /CE3 and /CE4) are used to enable the module's 4 bytes independently. Output enable(/OE) and write enable(/WE) can set the memory input and output.

Data is written into the SRAM memory when write enable (/WE) and chip enable (/CE) inputs are both LOW.

Reading is accomplished when /WE remains HIGH and /CE and output enable (/OE) are LOW.

For reliability, this SRAM module is designed as multiple power and ground pin. All module components may be powered from a single +5V DC power supply and all inputs and outputs are fully TTL-compatible.

FEATURES

- ◆ Access times : 12, 15 and 20ns
- ◆ High-density 512KByte design
- ◆ High-reliability, high-speed design
- ◆ Single + 5V $\pm 0.5V$ power supply
- ◆ Easy memory expansion with /CE and /OE functions
- ◆ All inputs and outputs are TTL-compatible
- ◆ Industry-standard pinout
- ◆ FR4-PCB design

OPTIONS

MARKING

- ◆ Timing

8ns access	- 8
10ns access	-10
12ns access	-12
15ns access	-15
20ns access	-20
- ◆ Packages

64-pin SIMM	M
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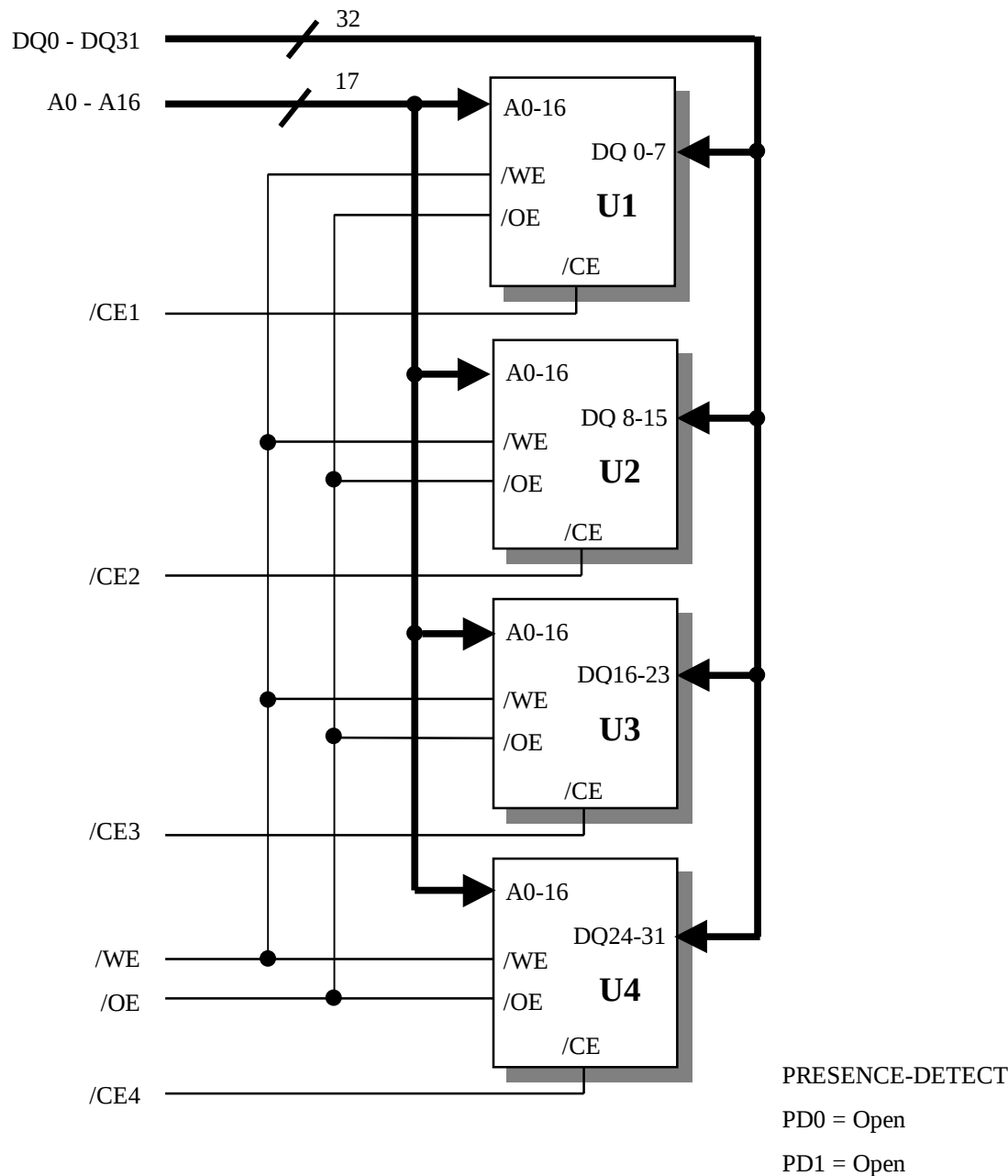
PIN ASSIGNMENT

Vss	1		/CE4	33	
PD0	2		/CE3	34	
PD1	3		NC	35	
DQ0	4		A16	36	
DQ8	5		/OE	37	
DQ1	6		Vss	38	
DQ9	7		DQ24	39	
DQ2	8		DQ16	40	
DQ10	9		DQ25	41	
DQ3	10		DQ17	42	
DQ11	11		DQ26	43	
Vcc	12		DQ18	44	
A0	13		DQ27	45	
A7	14		DQ19	46	
A1	15		A3	47	
A8	16		A10	48	
A2	17		A4	49	
A9	18		A11	50	
DQ12	19		A5	51	
DQ4	20		A12	52	
DQ13	21		Vcc	53	
DQ5	22		A13	54	
DQ14	23		A6	55	
DQ6	24		DQ20	56	
DQ15	25		DQ28	57	
DQ7	26		DQ21	58	
Vss	27		DQ29	59	
/WE	28		DQ22	60	
A15	29		DQ30	61	
A14	30		DQ23	62	
/CE2	31		DQ31	63	
/CE1	32		Vss	64	

SIMM
TOP VIEW

PD0 = Open
 PD1 = Open

FUNCTIONAL BLOCK DIAGRAM



TRUTH TABLE

MODE	/OE	/CE	/WE	DQ	POWER
STANDBY	X	H	X	HIGH-Z	STANDBY
NOT SELECTED	H	L	H	HIGH-Z	ACTIVE
READ	L	L	H	Dout	ACTIVE
WRITE	X	L	L	Din	ACTIVE

ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING
Voltage on Any Pin Relative to Vss	$V_{IN,OUT}$	-0.5V to $V_{CC}+0.5V$
Voltage on Vcc Supply Relative to Vss	V_{CC}	-0.5V to +7.0V
Power Dissipation	P_D	4.0W
Storage Temperature	T_{STG}	-65°C to +150°C
Operating Temperature	T_A	0°C to +70°C

- ♦ Stresses greater than those listed under " Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS ($T_A=0$ to 70 °C)

PARAMETER	SYMBOL	MIN	TYP.	MAX
Supply Voltage	V_{CC}	4.5V	5.0V	5.5V
Ground	V_{SS}	0	0	0
Input High Voltage	V_{IH}	2.2	-	$V_{CC}+0.5V^{**}$
Input Low Voltage	V_{IL}	-0.5*	-	0.8V

* $V_{IL}(\text{Min.}) = -2.0V$ ac (Pulse Width $\leq 10ns$) for $I \leq 20$ mA

** $V_{IH}(\text{Min.}) = V_{CC}+2.0V$ ac (Pulse Width $\leq 10ns$) for $I \leq 20$ mA

DC AND OPERATING CHARACTERISTICS (1)(0°C $\leq T_A \leq 70$ °C ; $V_{CC} = 5V \pm 10\%$)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	MAX	UNITS
Input Leakage Current	$V_{IN}=V_{SS}$ to V_{CC}	IL_I	-2	2	μA
Output Leakage Current	$/CE=V_{IH}$ or $/OE=V_{IH}$ or $/WE=V_{IL}$ $V_{OUT}=V_{SS}$ to V_{CC}	IL_0	-2	2	μA
Output High Voltage	$I_{OH} = -4.0mA$	V_{OH}	2.4		V
Output Low Voltage	$I_{OL} = 8.0mA$	V_{OL}		0.4	V

* $V_{CC}=5.0V$, Temp=25 °C

DC AND OPERATING CHARACTERISTICS (2)

DESCRIPTION	TEST CONDITIONS	SYMBOL	MAX			UNIT
			-12	-15	-20	
Power Supply Current:Operating	Min. Cycle, 100% Duty /CE=V _{IL} , V _{IN} =V _{IH} or V _{IL} , I _{OUT} =0mA	I _{CC}	75	73	70	mA
Power Supply Current:Standby	Min. Cycle, /CE=V _{IH}	I _{SB}	30	30	30	mA
	f=0MHZ, /CE≥V _{CC} -0.2V, V _{IN} ≥ V _{CC} -0.2V or V _{IN} ≤0.2V	I _{SB1}	5	5	5	mA

CAPACITANCE (T_A =25 °C , f= 1.0Mhz)

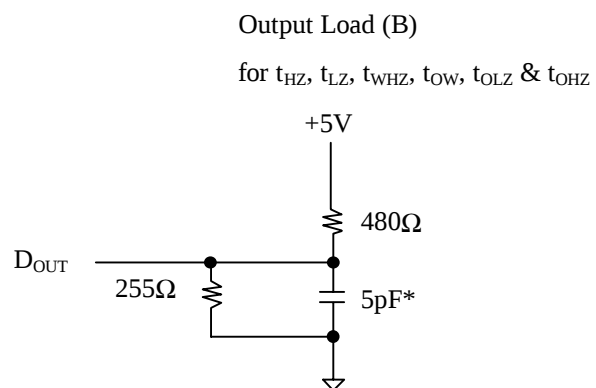
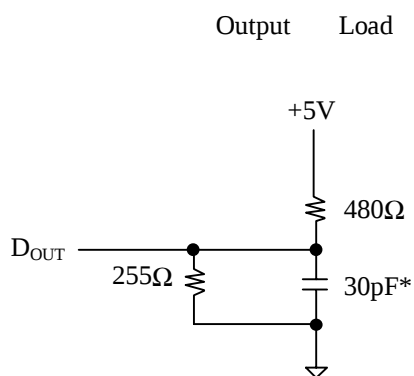
DESCRIPTION	TEST CONDITIONS	SYMBOL	MAX	UNIT
Input /Output Capacitance	V _{IO} =0V	C _{IO}	8	pF
Input Capacitance	V _{IN} =0V	C _{IN}	8	pF

* NOTE : Capacitance is sampled and not 100% tested

AC CHARACTERISTICS (0°C ≤ T_A ≤ 70 °C ; V_{CC} = 5V ± 0.5V, unless otherwise specified)

Test conditions

PARAMETER	VALUE
Input Pulse Level	0V to 3V
Input Rise and Fall Time	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	See below



READ CYCLE

PARAMETER	SYMBOL	-12		-15		-20		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
Read Cycle Time	t _{RC}	12		15		20		ns
Address Access Time	t _{AA}		12		15		20	ns

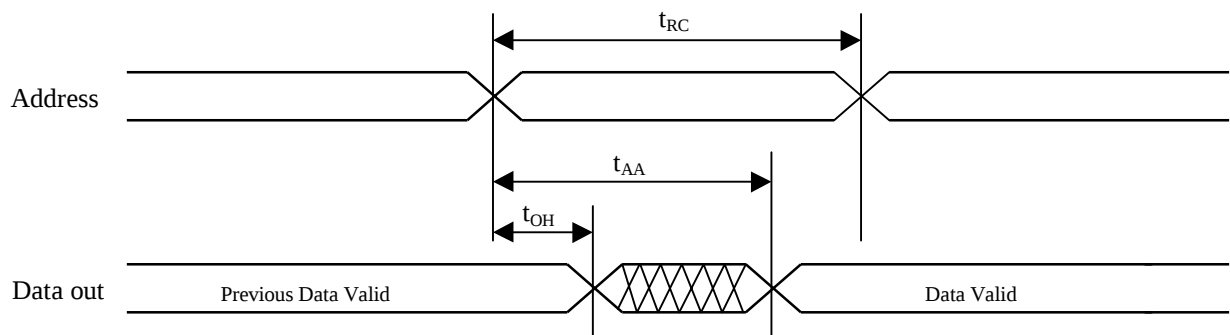
Chip Select to Output	t_{CO}		12		15		20	ns
Output Enable to Output	t_{OE}		6		7		9	ns
Output Enable to Low-Z Output	t_{OLZ}	0		0		0		ns
Chip Enable to Low-Z Output	t_{LZ}	3		3		3		ns
Output Disable to High-Z Output	t_{OHZ}	0	6	0	7	0	9	ns
Chip Disable to High-Z Output	t_{HZ}	0	6	0	7	0	9	ns
Output Hold from Address Change	t_{OH}	3		3		3		ns
Chip Select to Power Up Time	t_{PU}	0		0		0		ns
Chip Select to Power Down Time	t_{PD}	-	12		15		20	ns

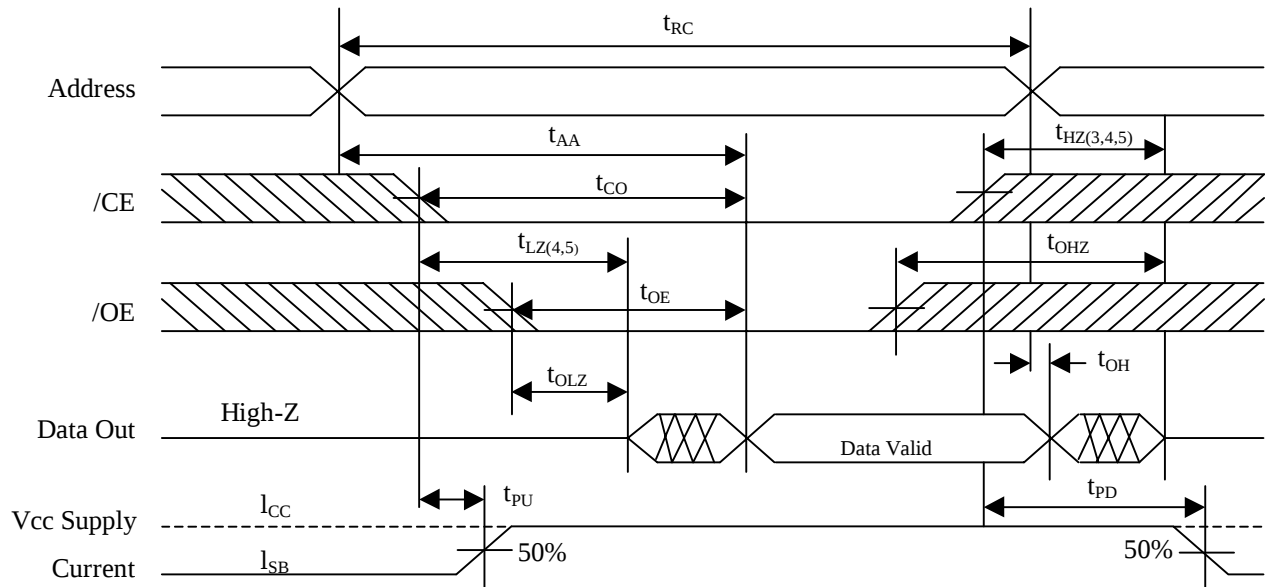
WRITE CYCLE

PARAMETER	SYMBOL	-12		-15		-20		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
Write Cycle Time	t_{WC}	12		15		20		ns
Chip Select to End of Write	t_{CW}	8		10		12		ns
Address Set-up Time	t_{AS}	0		0		0		ns
Address Valid to End of Write	t_{AW}	8		9		10		ns
Write Pulse Width	t_{WP}	8		9		10		ns
Write Recovery Time	t_{WR}	0		0		0		ns
Write to Output High-Z	t_{WHZ}	0	6	0	7	0	9	ns
Data to Write Time Overlap	t_{DW}	6		7		8		ns
Data Hold from Write Time	t_{DH}	0		0		0		ns
End of Write to Output Low-Z	t_{OW}	3		3		3		ns

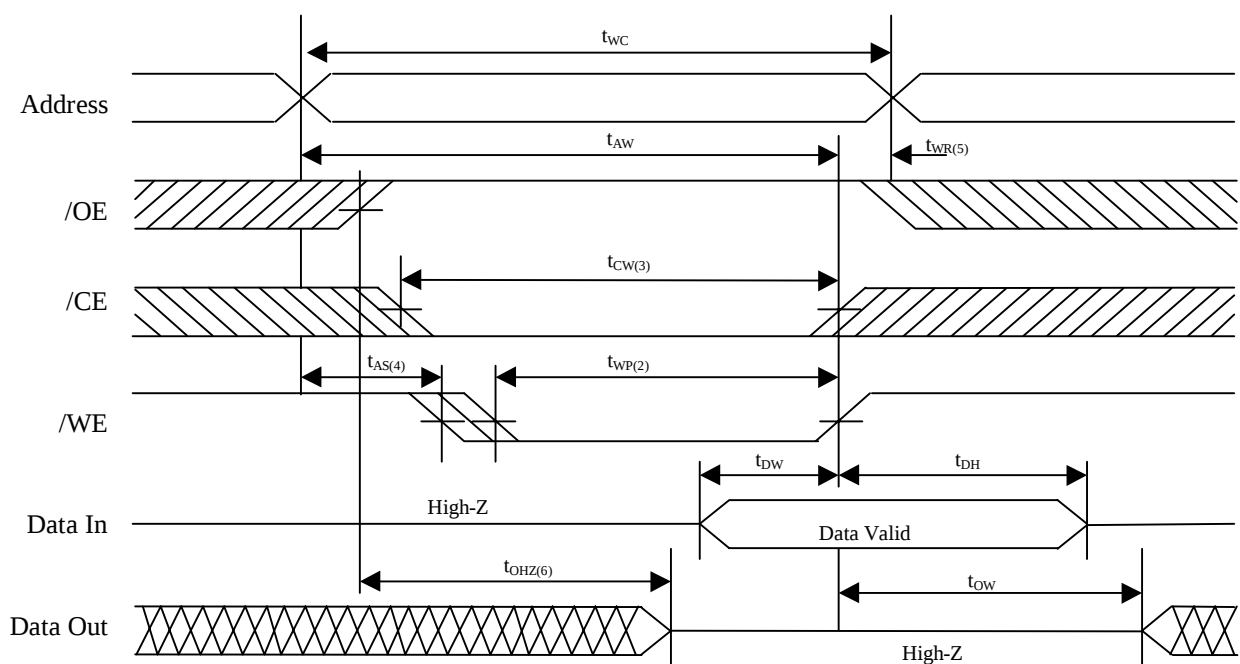
TIMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(Address Controlled) (/CE = /OE = V_{IL} , /WE = V_{IH})

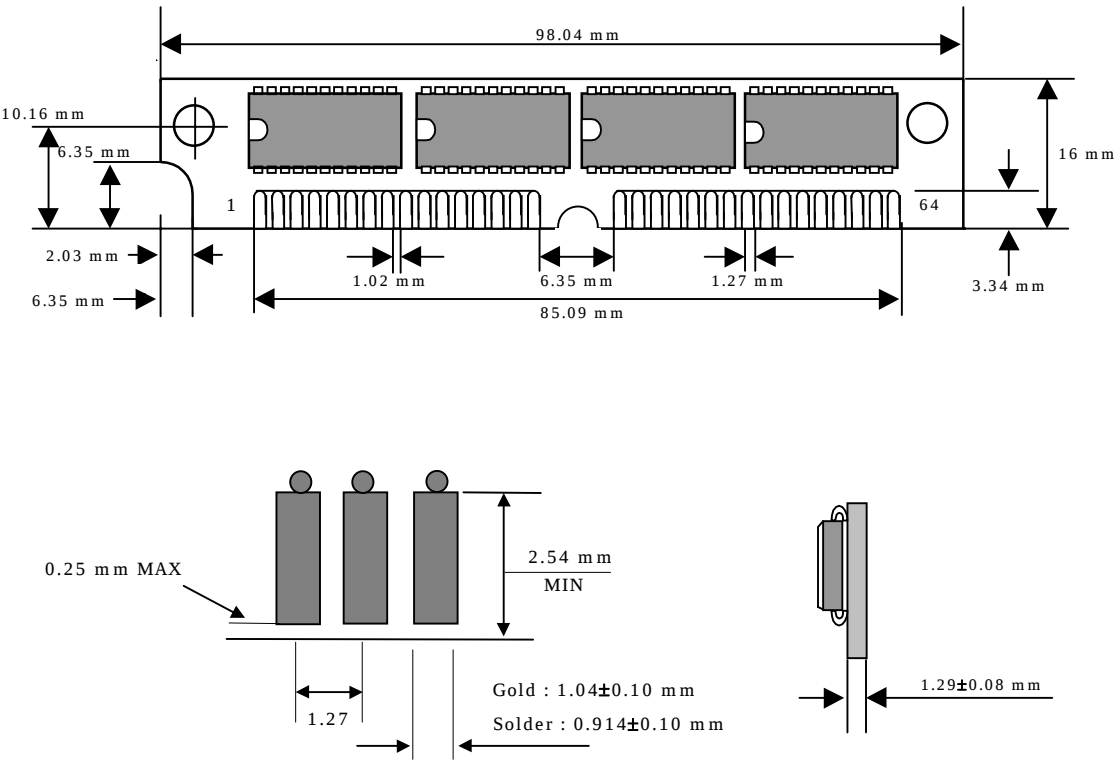


TIMING WAVEFORM OF READ CYCLE (/CE Controlled)**Notes (Read Cycle)**

1. /WE is high for read cycle.
2. All read cycle timing is referenced from the last valid address to first transition address.
3. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit condition and are not referenced to V_{OH} or V_{OL} levels.
4. At any given temperature and voltage condition, t_{HZ} (max.) is less than t_{LZ} (min.) both for a given device and from device to device.
5. Transition is measured $\pm 200\text{mV}$ from steady state voltage with Load (B). This parameter is sampled and not 100% tested.
6. Device is continuously selected with /CE = V_{IL} .
7. Address valid prior to coincident with /CE transition low.

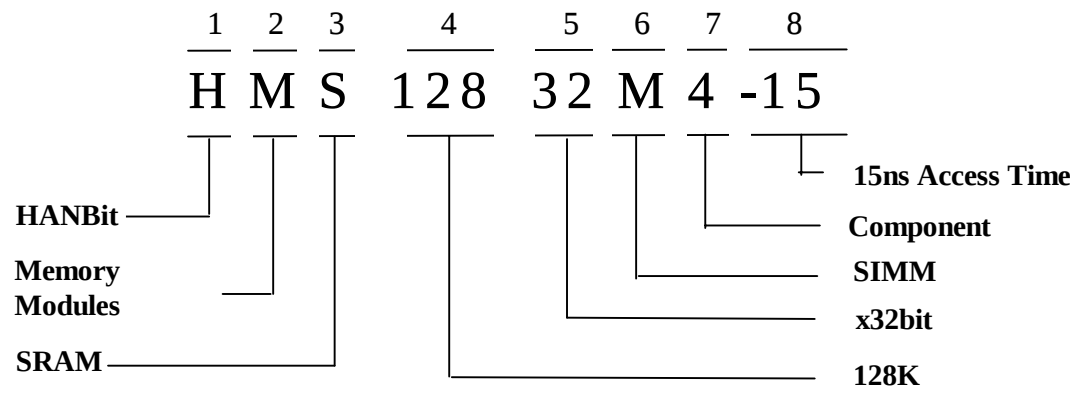
TIMING WAVEFORM OF WRITE CYCLE (/OE=Clock)

PACKAGING INFORMATION



(Solder & Gold Plating Lead)

ORDERING INFORMATION



- 1. - Product Line Identifier
HANBit ----- H
- 2. - Memory Modules
- 3. - SRAM
- 4. - Depth : 128K
- 5. - Width : x 32bit
- 6. - Package Code
SIMM ----- M
- 7. - Number of Memory Components
- 8. - Access time
 - 10 ----- 10ns
 - 12 ----- 12ns
 - 15 ----- 15ns
 - 17 ----- 17ns
 - 20 ----- 20ns